



浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO.,LTD.

产品规格书

Specification of products

产品名称：可控硅模块

产品型号：MFC27A-T02

浙江世菱半导体有限公司
ZHEJIANG SHILING SEMICONDUCTOR CO., LTD.

地址：浙江省 丽水市 莲都区

电话：(0578) 3012571 3615078

传真：(0578) 3611180

邮编：323000

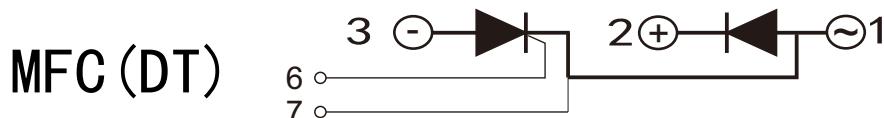
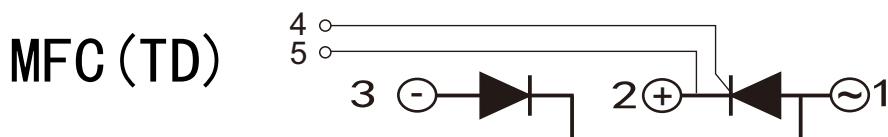
E-mail: smrshiling01@163.com

[Http://www.smrshiling.com](http://www.smrshiling.com)

拟制	审核	核准
林益龙	曹剑龙	宗瑞

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T _j (°C)	VALUE			UNIT
				Min	Type	Max	
I _{T(AV)}	Mean on-state current	180° half sine wave 50Hz Single side cooled, T _C =85°C	125			27	A
I _{T(RMS)}	RMS on-state current	Single side cooled, T _C =85°C	125			43	A
V _{DRM} V _{RRM}	Repetitive peak off-state voltage Repetitive peak reverse voltage	V _{DRM} &V _{RRM} tp=10ms V _{DsM} &V _{RsM} = V _{DRM} &V _{RRM} +200V respectively	125	600		2000	V
I _{DRM} I _{RRM}	Repetitive peak current	at V _{DRM} at V _{RRM}	125			10	mA
I _{TSM}	Surge on-state current	10ms half sine wave	125			0.48	KA
I ² t	I ² T for fusing coordination	V _R =60%V _{RRM}				1.5	A ² s*10 ³
V _{TO}	Threshold voltage		125			0.90	V
r _T	On-state slop resistance					12	mΩ
V _{TM}	Peak on-state voltage	I _{TM} =50A	25			1.40	V
V _{FM}	Peak on-state voltage	I _{FM} =50A	25			1.10	V
dv/dt	Critical rate of rise of off-state voltage	V _{DM} =67%V _{DRM}	125			1000	V/μs
di/dt	Critical rate of rise of on-state current	From 67%V _{DRM} to 210A, Gate source 1.5A t _r ≤0.5 μ sRepetitive	125			110	A/ μs
I _{GT}	Gate trigger current		25	30		150	mA
V _{GT}	Gate trigger voltage	V _A =12V, I _A =1A		0.8		1.8	V
I _H	Holding current			20		100	mA
V _{GD}	Non-trigger gate voltage	At 67%V _{DRM}	125			0.25	V
R _{th(j-c)}	Thermal resistance Junction to heatsink	At 180° sine Single side cooled				0.280	°C /W
V _{iso}	Isolation voltage	50Hz, RM. S, t=1min, I _{iso} : 1mA (MAX)		2500			V
F _m	Thermal connection torque(M5)				4.0		N.m
	Mounting torque(M6)				5.0		N.m
T _{Stg}	Stored temperature			-40		125	°C
W _t	Weight				122		g
Outline							

OUTLINE DRAWING & CIRCUIT DIAGRAM



Rating and Characteristic

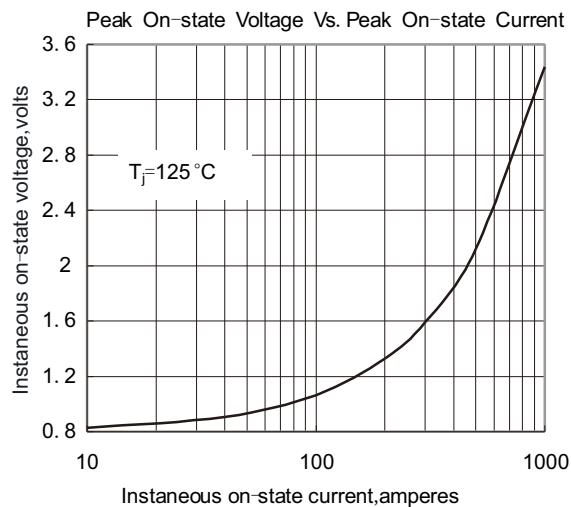


Fig. 1

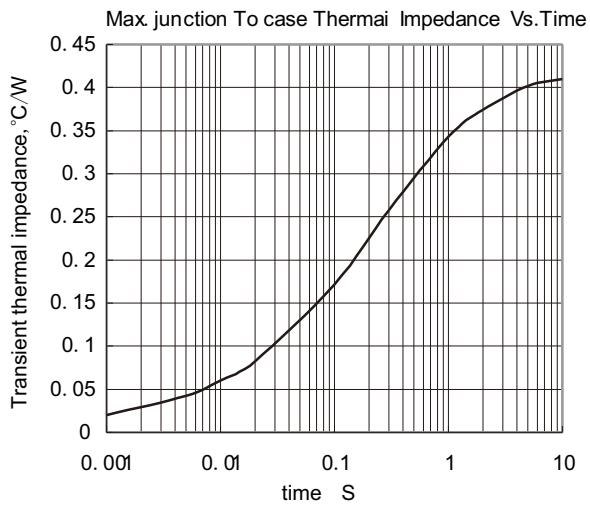


Fig. 2

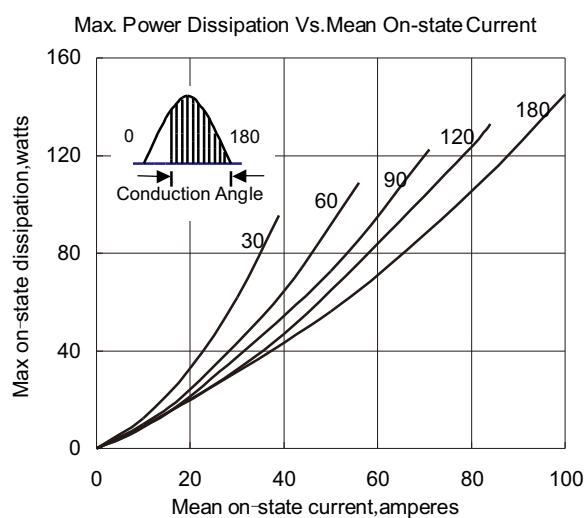


Fig. 3

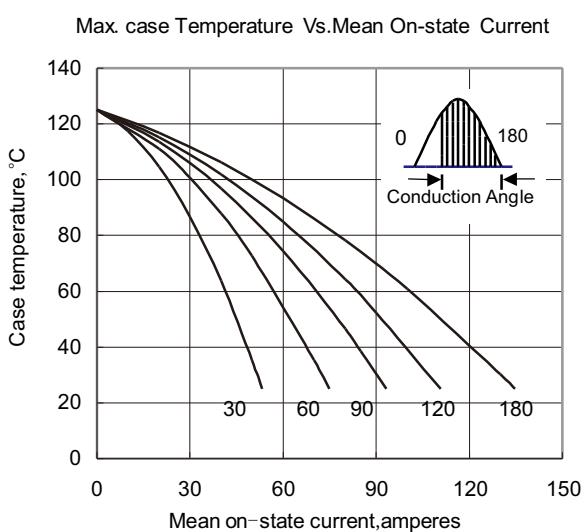


Fig. 4

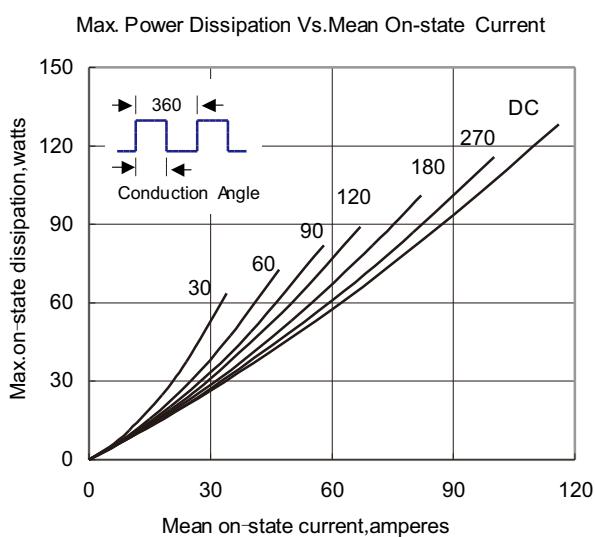


Fig. 5

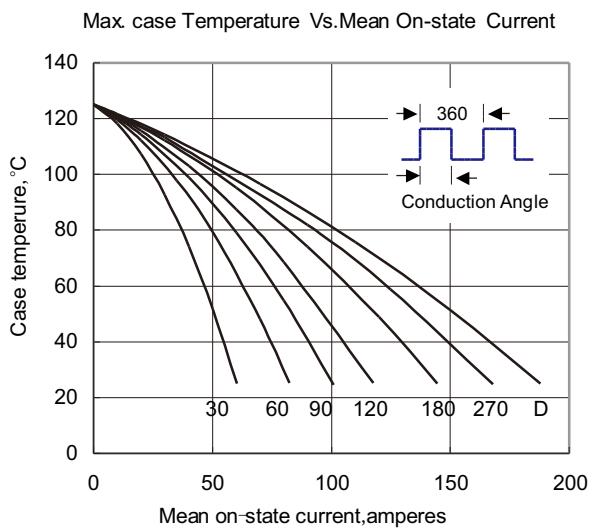


Fig. 6

Rating and Characteristic

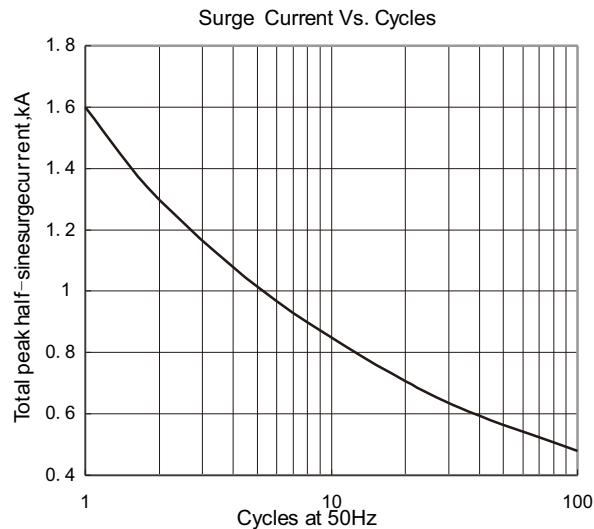


Fig. 7

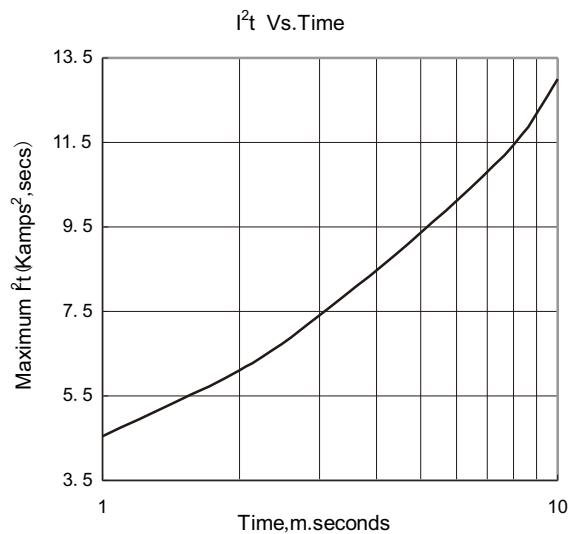


Fig. 8

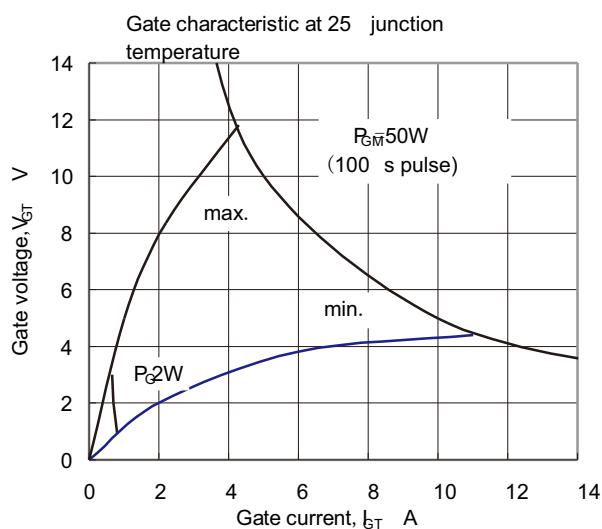


Fig. 9

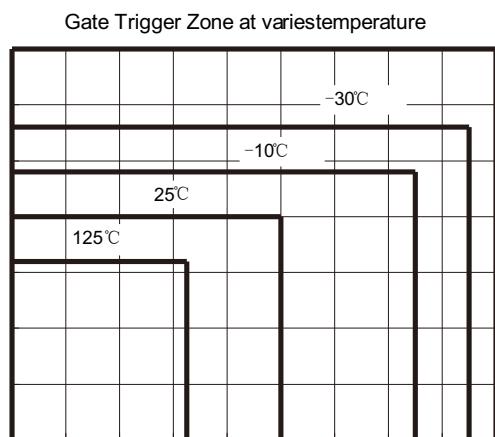


Fig. 10

Outside Dimension

